

PR2001G - PR2007G

FAST RECOVERY GLASS PASSIVATED RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 2.0 A

Features

- Glass Passivated Die Construction
- Diffused Junction
- Fast Switching for High Efficiency
- High Current Capability and Low Forward Voltage Drop
- Surge Overload Rating to 80A Peak
- Low Reverse Leakage Current
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

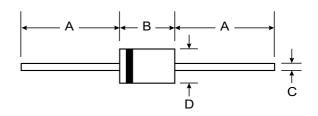
Case: DO-15Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208
Polarity: Cathode Band
Marking: Type Number
Weight: 0.4 grams (approx.)







DO-15							
Dim	Min	Max					
Α	25.40	_					
В	5.50	7.62					
С	0.686	0.889					
D	2.60	3.60					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

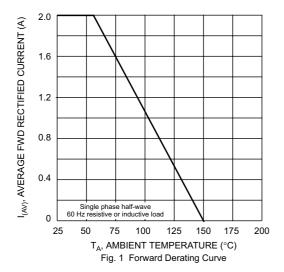
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

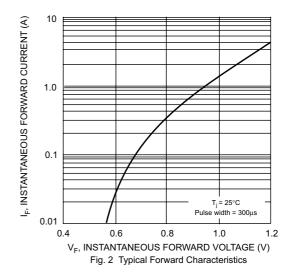
Characteristic		Symbol	PR 2001G	PR 2002G	PR 2003G	PR 2004G	PR 2005G	PR 2006G	PR 2007G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage		V _{R(RMS)}	35	70	140	280	420	560	700	٧
Average Rectified Output Current (Note 1) @ T _A = 55°C		lo	2.0							Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method)		I _{FSM}	80						Α	
Forward Voltage Drop	@ I _F = 2.0A		1.3							٧
Peak Reverse Current @ $T_A = 25^{\circ}C$ at Rated DC Blocking Voltage @ $T_A = 100^{\circ}C$		I _{RM}	5.0 100							μА
Reverse Recovery Time (Note 3)		t _{rr}	150			250	50	00	ns	
Typical Junction Capacitance (Note 2)		Cj	35							pF
Typical Thermal Resistance Junction to Ambient		$R_{\theta JA}$	50						K/W	
Operating and Storage Temperature Range		T _j , T _{STG}	-65 to +150						°C	

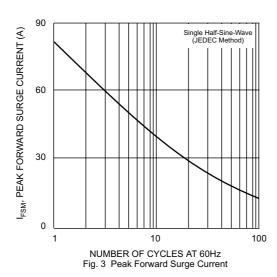
Notes:

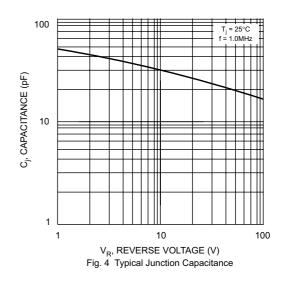
- 1. Valid provided that leads are maintained at ambient temperature at a distance of 9.5mm from the case.
- 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 3. Measured with I_F = 0.5A, I_R = 1.0A, I_{rr} = 0.25A. See figure 5.

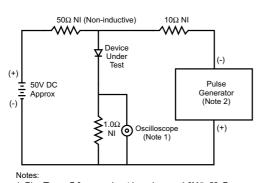


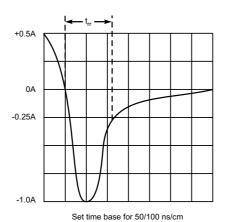












- 1. Rise Time = 7.0ns max. Input Impedance = $1.0M\Omega$, 22pF.
- 2. Rise Time = 10ns max. Input Impedance = 50Ω .

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit